

Ultra low capacitance unidirectional double ESD protection diode

10 April 2014

Product data sheet

### 1. General description

Ultra low capacitance unidirectional double ElectroStatic Discharge (ESD) protection diode in a DFN1006-3 (SOT883) leadless ultra small Surface-Mounted Device (SMD) plastic package designed to protect up to two signal lines from the damage caused by ESD and other transients.

### 2. Features and benefits

- Ultra low diode capacitance: C<sub>d</sub> = 0.80 pF
- ESD protection up to 15 kV; IEC61000-4-2
- I<sub>PPM</sub> = 2.5 A; IEC 61643-321 (surge)
- AEC-Q101 qualified

### 3. Applications

- High-speed data lines
- Portable electronics

. . .

- Communication systems
- Computers and peripherals

### 4. Quick reference data

1.1.1

Table 1. Qui	ck reference data						
Symbol Parameter		Conditions		Min	Тур	Max	Unit
Per diode							
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0 V	[1]	-	0.8	0.95	pF
V <sub>RWM</sub>	reverse standoff voltage			-	-	5	V

[1] Measured from pin 1 or 2 to 3.



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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K1	cathode (diode 1)	1	1
2	K2	cathode (diode 2)	2	
3	А	common anode	Transparent top view	brb051
			DFN1006-3 (SOT883)	

# 6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
PESD5V0X2UAM	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PESD5V0X2UAM	ZJ

### 8. Limiting values

#### Table 5. Limiting values

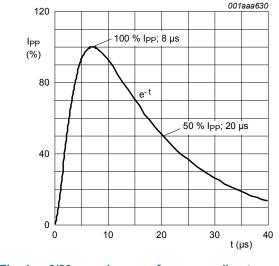
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode			1			
I <sub>PPM</sub>	rated peak pulse current	t <sub>p</sub> = 8/20 μs	[1][2]	-	2.5	А
Tj	junction temperature			-	150	°C
T <sub>stg</sub>	storage temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
ESD maxim	num ratings	1				
V <sub>ESD</sub>	electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	<u>[3][2]</u>	-	15	kV
		IEC 61000-4-2 (air discharge)	[3][2]	-	15	kV
		machine model	[2]	-	400	V
		MIL-STD-883 (human body model)		-	10	kV

[1] According to IEC 61000-4-5 and IEC 61643-321.

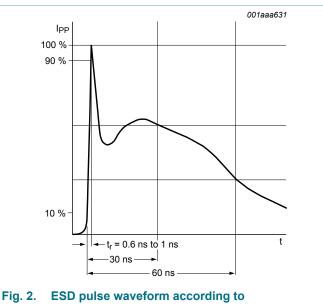
Measured from pin 1 or 2 to 3.

[3] Device stressed with ten non-repetitive ESD pulses.



[2]

Fig. 1. 8/20 µs pulse waveform according to IEC 61000-4-5 and IEC 61643-321



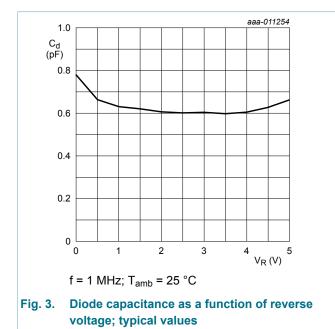
IEC 61000-4-2

#### **Characteristics** 9.

Table 6. O	Characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per diode							
V <sub>RWM</sub>	reverse standoff voltage			-	-	5	V
I <sub>RM</sub>	reverse leakage current	V <sub>R</sub> = 5 V	[1]	-	1	10	nA
V <sub>CL</sub>	clamping voltage	I <sub>PP</sub> = 1 A; t <sub>p</sub> = 8/20 μs	[2][1]	-	-	13	V
		I <sub>PP</sub> = 2.5 A; t <sub>p</sub> = 8/20 μs	[2][1]	-	-	14	V
V <sub>BR</sub>	breakdown voltage	I <sub>R</sub> = 10 mA	[1]	7.5	8.8	10	V
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0 V	[1]	-	0.8	0.95	pF
R <sub>dyn</sub>	dynamic resistance	I <sub>R</sub> = 10 A	[3][1]	-	0.65	-	Ω

[1] Measured from pin 1 or 2 to 3.

- [2] [3]
- According to IEC 61000-4-5 and IEC 61643-321. Non-repetitive current pulse, Transmission Line Pulse (TLP); square pulse; ANSI / ESD STM5.5.1-2008.



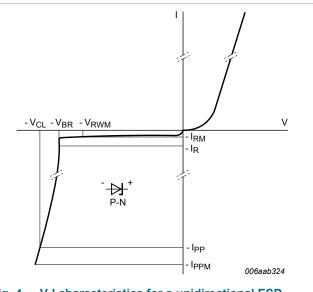
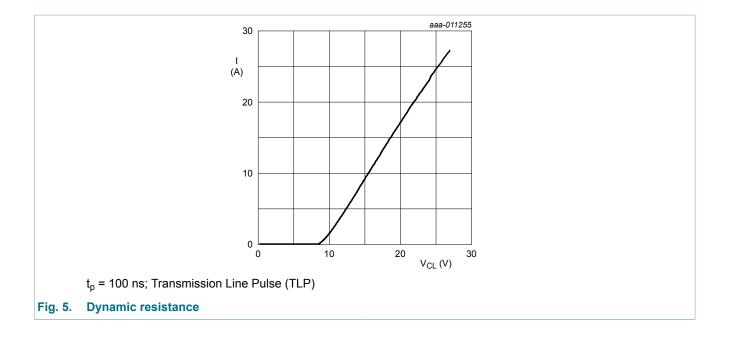


Fig. 4. V-I characteristics for a unidirectional ESD protection diode

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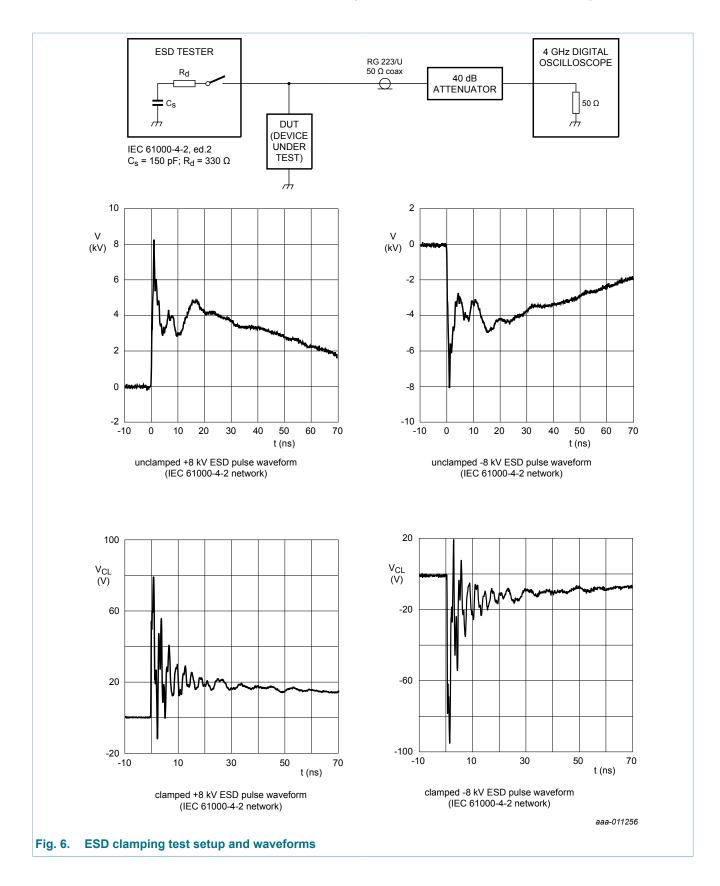
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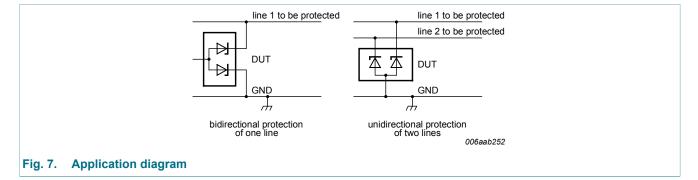
### **10. Test information**

#### **10.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

### **11. Application information**

The device is designed for the protection of up to two unidirectional data lines from surge pulses and ESD damage.



#### Circuit board layout and protection device placement

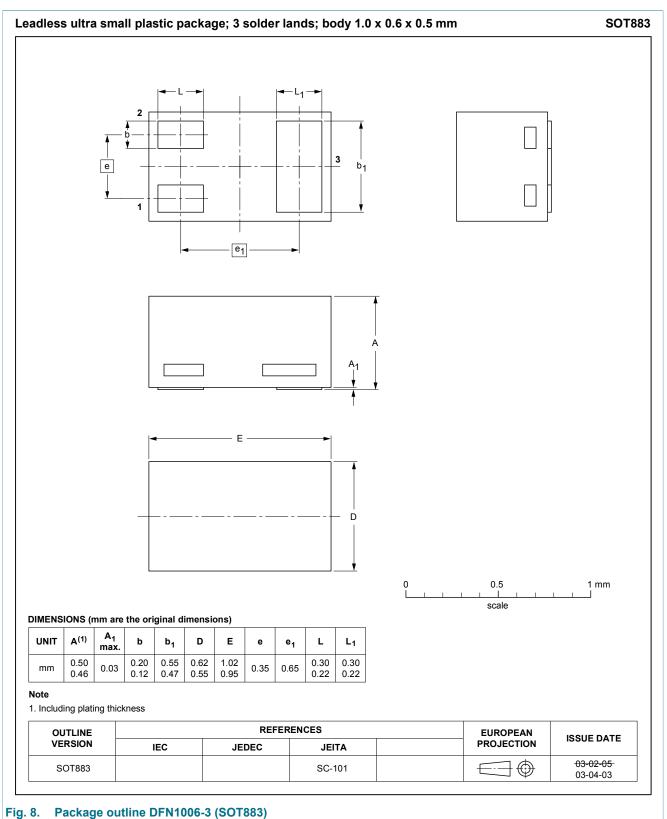
Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the device as close to the input terminal or connector as possible.
- 2. Minimize the path length between the device and the protected line.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Use ground planes whenever possible. For multilayer PCBs, use ground vias.

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### 12. Package outline

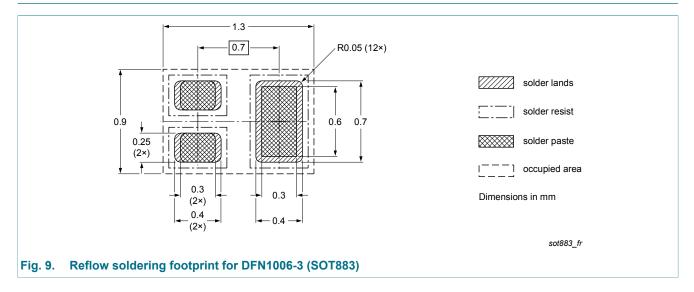


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## 13. Soldering



# 14. Revision history

Table 7. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PESD5V0X2UAM v.1	20140410	Product data sheet	-	-	

#### Ultra low capacitance unidirectional double ESD protection diode

#### **15. Legal information**

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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